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Roll No. ....

**328453(28)**

**B. E. (Fourth Semester) Examination,  
April-May 2021**

**(New Scheme)**

**(Electronics & Telecommunication Engg. Branch)**

**ANALOG ELECTRONICS**

***Time Allowed : Three hours***

***Maximum Marks : 80***

***Minimum Pass Marks : 28***

***Note : Attempt all questions. Part (a) of each unit is compulsory carry 2 marks. Attempt any two parts from (b), (c) and (d) carry 7 marks. Assume suitable data if required.***

**Unit-I**

1. (a) Which configuration is known as emitter follower and why?
- (b) Draw the hybrid model for all the three configurations of BJT and give the equations.

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(c) A transistor used in CE arrangement has the following set of  $h$  parameters when the d.c. operating point is  $V_{CE} = 10$  volts and  $I_C = 1$  mA :  $h_{ie} = 200 \Omega$ ;  $h_{oe} = 10^{-4}$  mho;  $h_{re} = 10^{-3}$ ;  $h_{fe} = 50$ .

Determine (i) input impedance (ii) current gain, and (iii) voltage gain.

The a.c. load seen by the transistor is  $rL = 600 \Omega$ .

What will be approximate values using reasonable approximations?

(d) Draw the  $h$ -parameter equivalent circuit for a generalized transistorized amplifier and derive the expression only for  $A_p$ ,  $A_v$ , and  $R_i$ .

### Unit-II

2. (a) What is  $r_{b'b}$ ? How does it respond to temperature?

(b) Prove that :

$$(i) h_{fe} = g_m r_{b'e}$$

$$(ii) h_{ie} = r_{b'b} + r_{b'e}$$

$$(iii) r_{b'e} = \frac{r_{b'c}}{h_{re}}$$

[ 3 ]

(c) The following transistor measurements are made at  $I_C = 5$  mA,  $V_{CE} = 10$  V at room temperature,  $h_{fe} = 100$ ,  $h_{ie} = 600 \Omega$ .

$$|A_{ie}| = 10 \text{ at } 10 \text{ MHz, } C_c = 3 \text{ pF}$$

Find  $F_\beta$ ,  $F_T$ ,  $C_e$ ,  $r_{b'e}$ ,  $r_{bb'}$ .

(d) Derive the equation for  $g_m$ , which give the relation between  $g_m$ ,  $I_C$  and temperature.

### Unit-III

3. (a) Define rise time of an amplifier. How it is related with upper 3 dB frequency of the amplifier?

(b) Prove that the bandwidth shrinks in cascading of identical non-interacting stages.

(c) It is desired that the voltage gain of the RC coupled amplifier at 60 Hz should not decrease by more than 10% from its midband value. Show that the coupling capacitance  $C$  must be at least equal to  $5.5/R'$ , where  $R' = R'_0 + R'_1$  and is expressed in kilohms and  $C$  in microfarads.

(d) Show that the maximum conversion efficiency of the idealized class B push-pull amplifier circuit is 78.5%.

**Unit-IV**

4. (a) What do you mean by negative feedback?
- (b) Give step procedure for identifying topology of feedback in amplifiers.
- (c) Derive the derivation of input resistance and output resistance of voltage shunt feedback amplifier.
- (d) Discuss the consequences of introducing negative feedback in small signal amplifier.

**Unit-V**

5. (a) What is the Barkhausen criterion for the feedback oscillators?
- (b) Explain the operational characteristics of RC phase shift oscillator and prove that  $h_{fe \text{ min}} = 44.5$ .
- (c) Draw the circuit of Wein bridge oscillator and explain its working principle. Derive the expression for frequency of oscillations.
- (d) Draw the circuit of Colpitts oscillator. How are the feedback requirements met in it? Derive the expression for frequency of oscillations.